

Contents

List of Principal Symbols

xvi

1. Some Basic Concepts Related to Electrical Transport in Organic Semiconductors

1

1.1. Concepts of π -electrons, σ -electrons, localized and delocalized orbitals and states	1
1.2. The energy band model	7
1.2.1. Carrier drift mobility	11
(A) Temperature dependence of mobility	14
(B) Isotope effect	15
(C) Pressure dependence of mobility	16
1.2.2. Hall effect	17
1.3. The tunnelling model	19
1.4. The hopping model	21
1.5. Polarons in molecular crystals	27
1.6. Dark electric conduction	33
1.6.1. The activation energy	33
1.6.2. The compensation effect	36
1.6.3. The conformons	37
1.6.4. The anisotropy	38
1.6.5. The frequency dependence	39
1.7. Thermoelectric effects	42
1.8. Carrier generation	49
1.8.1. Injection of carriers from electrodes	49
1.8.2. Intrinsic excitation	49
1.8.3. Extrinsic excitation	51
1.8.4. Field-assisted generation	51
1.9. Formation of traps	51
1.9.1. Structural defects excluding impurities	52
(A) Point defects	52
(B) Other structural defects	55
1.9.2. Defects due to chemical impurities	58
1.10. Lifetime and relaxation electric conduction	59
1.10.1. The concept of the lifetime regime	59
1.10.2. The concept of the relaxation regime	61

2. Charge Carrier Injection from Contacts

64

2.1. Concepts of electrical contacts, potential barriers, and electric conduction	64
2.1.1. Electrical contacts, work functions, and contact potentials	65
2.1.2. Types of electrical contacts	73
(A) Neutral contacts	73
(B) Blocking contacts	75
(C) Ohmic contacts	76

xi

(D) Metal–electrolyte contacts	83
(E) Electrolyte–semiconductor (or –insulator) contacts	83
2.1.3. Surface states	86
2.2. Charge carrier injection through potential barriers from contacts	90
2.2.1. The lowering of the potential barrier and the Schottky effect	90
(A) Neutral contacts	91
(B) Blocking contacts	92
2.2.2. Field-enhanced thermionic emission	95
(A) The effect of effective mass	95
(B) The correction due to the drift and diffusion of carriers in the depletion region	96
(C) The effects of phonon-scattering and quantum mechanical reflection	99
2.2.3. Field emission	101
2.2.4. Thermionic field emission	108
2.3. Tunnelling through thin insulating films	110
2.3.1. A generalized potential barrier	110
2.3.2. A rectangular potential barrier	114
(A) Between dissimilar electrodes	114
(B) Between similar electrodes	119
(C) Some comparisons of the theory with experiments	121
2.3.3. Elastic and inelastic tunnelling	124
2.3.4. A metal–thin insulating film–semiconductor (MIS) system	128
2.3.5. Effects of space charge and traps, and impurity conduction	136
3. Space Charge Electric Conduction—One-carrier Current Injection	145
3.1. Some concepts relevant to space charge electric conduction	145
3.2. One-carrier (single) planar injection in solids	150
3.2.1. Theory	150
(A) Without traps	151
(B) The traps confined in single or multiple discrete energy levels	154
(C) The traps distributed exponentially within the forbidden energy gap	159
(D) The traps distributed Gaussianly within the forbidden energy gap	161
(E) The traps confined in smeared discrete energy levels	164
(F) The traps distributed uniformly within the forbidden energy gap	165
3.2.2. The scaling rule	166
3.2.3. Some comparisons of the theory with experiments	170
(A) Without traps	170
(B) The traps confined in single or multiple discrete energy levels	171
(C) The traps distributed exponentially within the forbidden energy gap	175
(D) The traps distributed Gaussianly within the forbidden energy gap	184
(E) The traps confined in smeared discrete energy levels	187
(F) The traps distributed uniformly within the forbidden energy gap	188
3.3. One-carrier (single) injection from a non-planar contacting electrode	189
3.3.1. Spherical injecting contacts without considering thermally generated free carriers	189
(A) Without traps	191
(B) With shallow traps confined in single discrete energy levels	192
(C) With traps distributed exponentially within the forbidden energy gap	193
3.3.2. Cylindrical injecting contacts without considering thermally generated free carriers	193
(A) Without traps	194
(B) With shallow traps confined in single discrete energy levels	195
(C) With traps distributed exponentially within the forbidden energy gap	195
3.3.3. Spherical injecting contacts with thermally generated free carriers	197
(A) Without traps	197
(B) With traps	200
3.4. The electrolyte–insulator systems	202
3.4.1. The exchange currents	203
3.4.2. Equilibrium properties of the electrolyte–insulator interface	205
(A) Theory	205
(B) Computed results and discussion	213

3.4.3. The current–voltage characteristics of an electrolyte–insulator system with traps of various distributions in energy and in space inside the insulator	215
(A) Theory	216
(B) Some typical results and discussion	222

4. Space Charge Electric Conduction—Two-carrier Current Injection 227

4.1. Definitions and physical concepts of terms related to trapping and recombination processes	227
4.1.1. Capture rates and capture cross-sections	228
4.1.2. Recombination rates and recombination cross-sections	230
4.1.3. Demarcation levels	231
4.1.4. Coulombic traps	235
4.1.5. Free electron – free hole recombination	238
4.1.6. Characteristic times	240
4.2 Kinetics of the recombination processes	242
4.2.1. Without recombination centres and without traps (band-to-band recombination)	243
4.2.2. With a single set of recombination centres but without traps	246
4.2.3. With a single set of recombination centres and with traps	249
4.2.4. With two levels of recombination centres but without traps	250
4.2.5. With multilevels of recombination centres but without traps	252
4.2.6. The Auger effect	253
4.3. Two-carrier (double) planar injection in solids	257
4.3.1. Without recombination centres and without traps	258
4.3.2. Without recombination centres but with traps	265
(A) The traps confined in single or multiple discrete energy levels	266
(B) The traps distributed Gaussianly in energy and uniformly in space	269
(C) The traps confined in smeared discrete energy levels	270
4.3.3. With recombination centres but without traps	270
(A) With small density of recombination centres	272
(B) With large density of recombination centres	276
(C) The effect of magnetic field on negative differential resistance	282
4.3.4. With recombination centres and with traps	285
4.3.5. The scaling rule	286

5. Electrical Transport under Special Conditions 288

5.1. Filamentary charge carrier injection in solids	288
5.1.1. Filamentary one-carrier (single) injection	288
5.1.2. Filamentary two-carrier (double) injection	293
5.2. The effect of carrier diffusion	298
5.2.1. One-carrier (single) injection	298
5.2.2. Two-carrier (double) injection	302
5.3. High field effects, Poole–Frenkel, and Onsager models	303
5.3.1. Transition from the bulk-limited to the electrode-limited conduction processes	303
5.3.2. Transition from the electrode-limited to the bulk-limited conduction processes	308
5.3.3. Transition from a single injection to a double injection process	310
5.3.4. Field dependent carrier mobilities	311
5.3.5. The Poole–Frenkel detrapping model	314
5.3.6. The Onsager model	322
5.4. Thermally stimulated detrapping and non-extrinsic electric conduction	325
5.4.1. Thermally stimulated currents	325
5.4.2. Thermally stimulated depolarization currents	331
5.4.3. Isothermal current decay	333
5.4.4. Non-extrinsic electric conduction	334
5.5. Current transient phenomena	337
5.5.1. One-carrier (single) planar injection transient currents	339
(A) The space-charge-free (SCF) transient	340
(B) The space-charge-limited (SCL) transient	345
(C) The space-charge-perturbed (SCP) transient	356

5.5.2.	Two-carrier (double) planar injection transient currents	359
(A)	In the absence of traps and diffusion	360
(B)	In the absence of diffusion but with traps	364
5.6.	Space charge electric conduction under time-varying fields	367
5.6.1.	One-carrier (single) planar injection	367
5.6.2.	Two-carrier (double) planar injection	370
5.7.	Charge carrier transport in relaxation semiconductors	375
5.7.1.	Minority carrier injection in relaxation semiconductors	375
(A)	Without traps	375
(B)	With traps	378
5.7.2.	Some comparisons of the theory with experiments	383
(A)	Current–voltage characteristics	384
(B)	Other properties	385
6.	Photoelectronic Processes	386
6.1.	Basic concepts	386
6.1.1.	Electronic states of molecules	386
6.1.2.	Dissociation of excitons	391
(A)	Exciton dissociation at electrode–semiconductor interfaces	392
(B)	Exciton dissociation due to interaction of excitons and trapped carriers	393
(C)	Auto-ionization (AI) processes	394
6.1.3.	Quantum yield and quantum efficiency for photoconduction	396
6.1.4.	Non-equilibrium steady state statistics	399
6.2.	Photoconduction	404
6.2.1.	Extrinsic photoconduction	406
(A)	Processes involving trapping and recombination centres	406
(B)	Processes involving excitons	418
6.2.2.	Intrinsic photoconduction	424
(A)	Band-to-band transition	426
(B)	Auto-ionization	429
6.3.	Photoemission	436
6.3.1.	Photoinjection from electrical contacts	436
(A)	Metallic contacts	436
(B)	Electrolytic contacts	442
6.3.2.	Photoemission from crystalline solids	444
(A)	Effects of surface conditions	449
(B)	Effects of imperfections in crystals	450
(C)	Electron energy distribution and energy loss relation	451
(D)	Multi-quantum processes	453
6.4.	Photovoltaic effects	453
6.4.1.	Bulk photovoltaic effects	453
(A)	The Dember effect	454
(B)	The photomagnetolectric effect	455
6.4.2.	Surface photovoltaic effects	455
(A)	Schottky barrier photovoltages	456
(B)	Photovoltaic effects in organic semiconductor–metal Schottky barriers	458
6.4.3.	Photovoltaic properties of p – n junctions	462
6.4.4.	Anomalous photovoltaic effects	463
7.	Luminescence	466
7.1.	Introductory remarks	466
7.1.1.	The Franck–Condon principle	468
7.1.2.	The radiative and non-radiative transition processes	470
7.2.	The formation and behaviour of excitons	477
7.2.1.	Dynamic properties of excitons	479
(A)	Free exciton – free exciton interactions	480
(B)	Free exciton – trapped exciton interactions	483
(C)	Exciton – charge carrier interactions	485

(D) Exciton – surface interactions	486
(E) Exciton – photon interactions	487
(F) Exciton – phonon interactions	487
7.2.2. Exciton transport processes	489
(A) Coherent transport	489
(B) Incoherent transport	491
7.2.3. Diffusion of excitons	492
(A) Diffusion of triplet excitons	493
(B) Diffusion of singlet excitons	497
7.3. Photoluminescence	503
7.3.1. Fluorescence	503
(A) Prompt fluorescence—theory	504
(B) Prompt fluorescence—experiments	508
(C) Delayed fluorescence—theory	518
(D) Delayed fluorescence—experiments	523
7.3.2. Phosphorescence	531
(A) Theory	531
(B) Experiments	534
7.4. Electroluminescence	537
7.4.1. Electroluminescence under time-invariant fields	538
(A) Theory	538
(B) Experiments	547
7.4.2. Electroluminescence under time-varying fields	551
(A) Pulsed electroluminescence	551
(B) Sinusoidal a.c. electroluminescence	555
7.4.3. Electroluminescence under magnetic fields	562
 Bibliography	 569
 Books	 569
 Articles	 571
 Index	 655